Comparison of Low Voltage Cathodoluminescent Phosphors

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Progress in field emission display (FED) technology requires the parallel development of phosphors that exhibit high cathodoluminescence (CL) efficiency at low voltage (< 1 kV) excitation and long term CL stability when subjected to high current densities. Five commercial phosphors, ZnO:Zn, YSiO₅:Ce, Y₂O₃:Eu, SrGa₂S₄:Ce and SrGa₂S₄:Eu have been studied using low voltage scanning cathodoluminescence microscopy and spectroscopy at 300 K. All samples were powders with a 0.5 – 10 μm particle size (Figure 1). ZnO:Zn was the only specimen that did not display any charging effects at 1 kV when using the in-lens secondary electron image mode, reflecting its good electrical conductivity compared with the other phosphors.

Dominant CL emission peaks were located at 495, 400, 615, 445 and 540 nm for ZnO:Zn, YSiO₅:Ce, Y₂O₃:Eu, SrGa₂S₄:Ce and SrGa₂S₄:Eu, respectively. Each emission peak was broad except for Y₂O₃:Eu which exhibited a sharp set of emission lines characteristic of Eu³⁺. A similar CL emission intensity was observed from every phosphor when excited under identical conditions at 1 kV. CL intensity, I_{CL}, versus beam current, I_B, measurements revealed that all phosphors displayed a power-law exponent of around m \approx 0.8 with I_{CL} \propto I_B^{0.8} over a wide range of I_B, 10 to 4000 pA (Figure 2). Although a threshold current of around 100 pA was found for SrGa₂S₄:Eu (Figure 3).

The emission lifetime for each phosphor was estimated using monochromatic CL images collected at pixel dwell time of $0.125~\mu s$ with frame integration to improve the signal to noise. Monochromatic CL images of YSiO₅:Ce (Figure 4), ZnO:Zn (Figure 5) and SrGa₂S₄:Ce (not shown) reveal little distortion in the direction of scan, indicating that these phosphors have radiative lifetimes (τ) < 1 μs . SrGa₂S₄:Eu (Figure 6) shows strong smearing indicative of emission lifetimes τ < 10 μs whereas gross streaking in Y₂O₃:Eu (not shown) points to τ > 100 μs .

This work has demonstrated the utility of low voltage scanning cathodoluminescence microscopy and spectroscopy for high resolution spatially resolved characterization of the luminescence properties of cathodoluminescent phosphors.

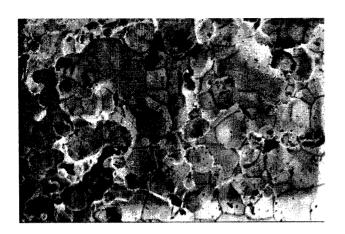


Fig. 1. CL image ZnO:Zn at 495 nm, 1 kV Horizontal Width of Field (HWF) = $58 \mu m$

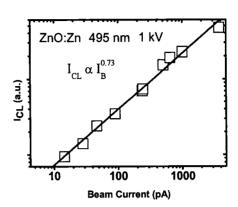


Fig. 2. I_{CL} versus I_B for ZnO:Zn at 1 kV

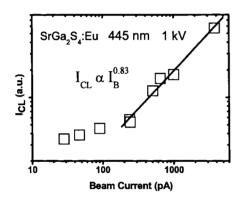


Fig. 3. I_{CL} versus I_B for SrGa₂S₄:Eu at 1 kV

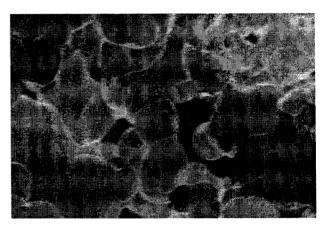


Fig. 4. CL image $SrGa_2S_4$:Ce at 445 nm and 1 kV, HWF = 24 μ m, line time = 128 μ s



Fig. 5. CL image ZnO:Zn at 495 nm and 1 kV HWF = $24 \mu m$, line time = $128 \mu s$



Fig. 6. CL image $SrGa_2S_4$:Eu at 540 nm and 1 kV, $HWF = 58 \mu m$, line time = 128 μs

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